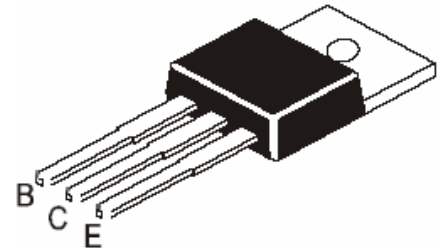


## Power Transistor (PNP)

### Features

- Application for Switching Regulators, Converters and Power Amplifiers
- Very low collector saturation voltage
- RoHS Compliant



TO-220



### Mechanical Data

<b>Case:</b>	TO-220, Plastic Package
<b>Terminals:</b>	Solderable per MIL-STD-202, Method 208
<b>Weight:</b>	0.08 ounces, 2.24 grams

### Maximum Ratings *(T<sub>Ambient</sub>=25°C unless noted otherwise)*

Symbol	Description	D45H11	Unit
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage	80	V
<b>V<sub>CES</sub></b>	Collector-Emitter Voltage	80	V
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage	5	V
<b>I<sub>C</sub></b>	Collector Current Continuous	10	A
<b>I<sub>CM</sub></b>	Collector Current Peak	20	A
<b>I<sub>B</sub></b>	Base Current	2	A
<b>P<sub>D</sub></b>	Total Power Dissipation at T <sub>C</sub> =25°C	50	W
	Total Power Dissipation Derate above 25°C	0.4	W/°C
<b>R<sub>θJC</sub></b>	Thermal Resistance from Junction to Case	2.5	°C/W
<b>T<sub>J</sub>, T<sub>STG</sub></b>	Operating Junction and Storage Temperature Range	-55 to +150	°C

# Power Transistor (PNP)

## D45H11

### Electrical Characteristics ( $T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	Min.	Max.	Unit	Conditions
<b>*hFE</b>	D.C. Current Gain	60	-		VCE=1.0V, IC=2.0A
		40	-		VCE=1.0V, IC=4.0A
<b>VCE(sus)</b>	Collector-Emitter Sustaining Voltage	80	-	V	IC=30mA, IB=0
<b>*VCE(sat)</b>	Collector-Emitter Saturation Voltage	-	1.0	V	IC=8.0A, IB=400mA
<b>*VBE(sat)</b>	Base-Emitter Saturation Voltage	-	1.5	V	IC=8.0A, IB=800mA
<b>ICES</b>	Collector-Emitter Cut-off Current	-	10	μA	VCE=80V, VBE=0
<b>IEBO</b>	Emitter-Base Cut-off Current	-	100	μA	VBE=5V, IC=0
<b>fT</b>	Current-Gain Bandwidth Product	12	-	MHz	VCE=10V, IC=0.5A, f=0.5MHz, fT= hfe  ° f test
<b>Cob</b>	Output Capacitance	400	-	pF	VCB=10V, IE=0, f=1.0MHz,
<b>tr</b>	Rise Time	-	0.6	μS	IC=5.0A, IB1=-IB2=500mA
<b>ts</b>	Storage Time	-	1.2		
<b>tf</b>	Fall Time	-	0.5		

\*Pulse Test: Pulse Width=300μs, Duty Cycle≤2%

### Typical Characteristics Curves

Fig.1- Power Derating

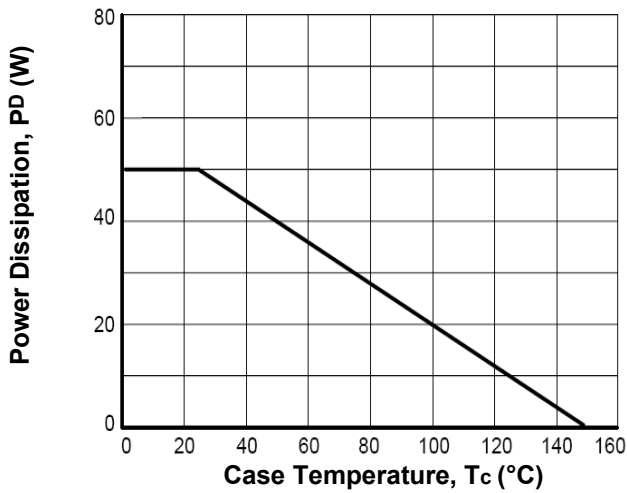


Fig.2-DC Current Gain

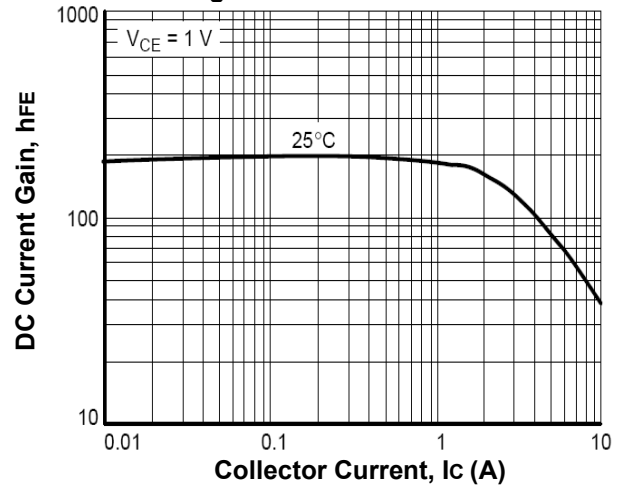


Fig.3- 'On' Voltages

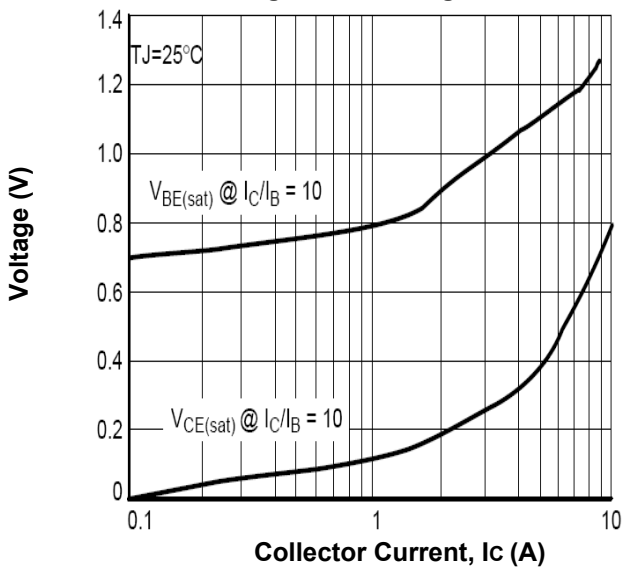
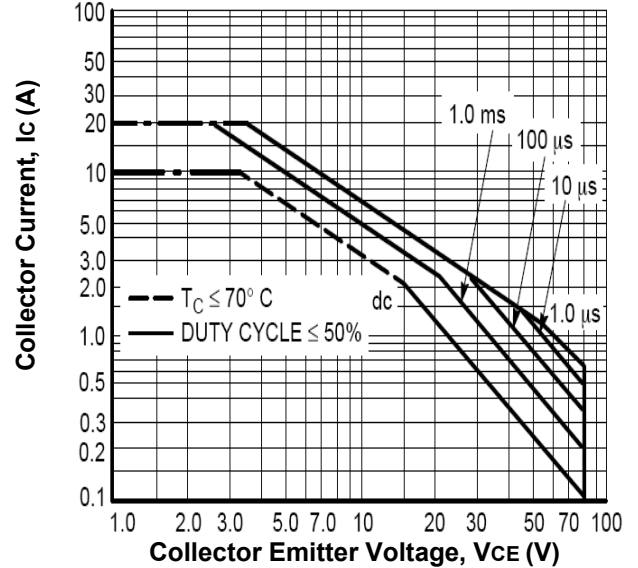
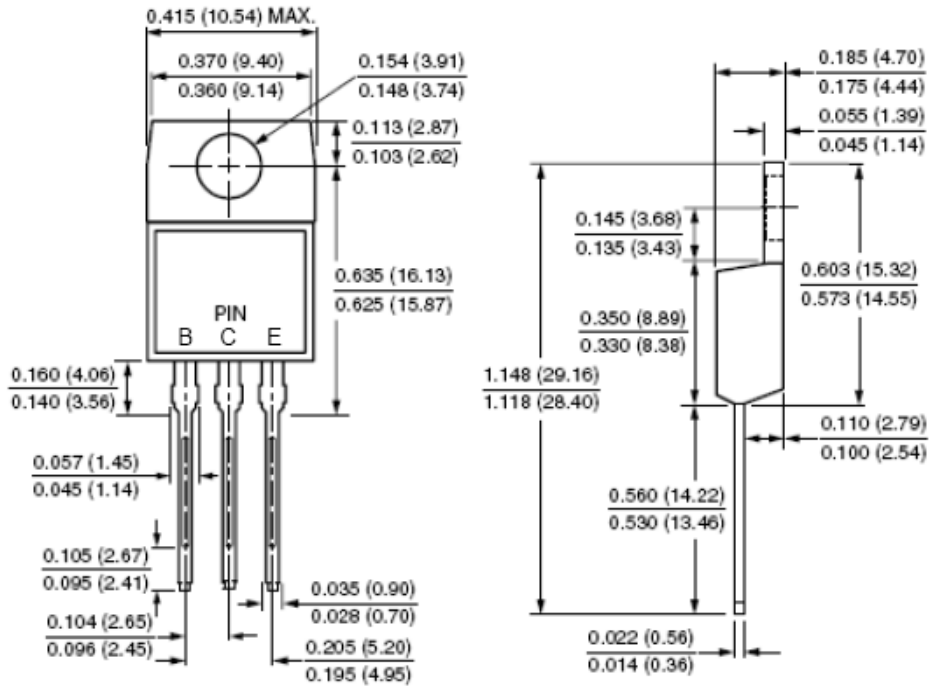


Fig.4- Forward Bias Safe Operating Area



Dimensions in inch (mm)

TO-220



Pin Configuration

- B. Base
- C. Collector
- E. Emitter

### How to contact us:

#### **US HEADQUARTERS**

28040 WEST HARRISON PARKWAY, VALENCIA, CA 91355-4162

Tel: (800) TAITRON (800) 824-8766 (661) 257-6060

Fax: (800) TAITFAX (800) 824-8329 (661) 257-6415

Email: [taitron@taitroncomponents.com](mailto:taitron@taitroncomponents.com)

Http://[www.taitroncomponents.com](http://www.taitroncomponents.com)

#### **TAITRON COMPONENTS MEXICO, S.A .DE C.V.**

BOULEVARD CENTRAL 5000 INTERIOR 5 PARQUE INDUSTRIAL ATITALAQUIA, HIDALGO C.P.  
42970 MEXICO

Tel: +52-55-5560-1519

Fax: +52-55-5560-2190

#### **TAITRON COMPONENTS INCORPORATED REPRESENTAÇÕES DO BRASIL LTDA**

RUA DOMINGOS DE MORAIS, 2777, 2.ANDAR, SALA 24 SAÚDE - SÃO PAULO-SP 04035-001 BRAZIL

Tel: +55-11-5574-7949

Fax: +55-11-5572-0052

#### **TAITRON COMPONENTS INCORPORATED, SHANGHAI REPRESENTATIVE OFFICE**

METROBANK PLAZA, 1160 WEST YAN' AN ROAD, SUITE 1503, SHANGHAI, 200052, CHINA

Tel: +86-21-5424-9942

Fax: +86-21-5424-9931